

## N-Channel Power MOSFET

600V, 11A, 0.38Ω

### FEATURES

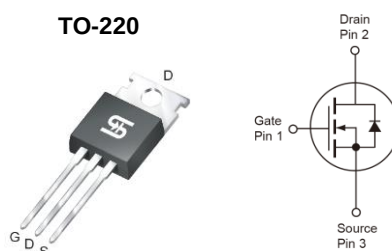
- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

### APPLICATION

- Power Supply
- Lighting

### KEY PERFORMANCE PARAMETERS

| PARAMETER          | VALUE | UNIT |
|--------------------|-------|------|
| $V_{DS}$           | 600   | V    |
| $R_{DS(on)}$ (max) | 0.38  | Ω    |
| $Q_g$              | 20.5  | nC   |



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| PARAMETER                                           |  |  |                        |  | SYMBOL                            | Limit        | UNIT |
|-----------------------------------------------------|--|--|------------------------|--|-----------------------------------|--------------|------|
| Drain-Source Voltage                                |  |  |                        |  | $V_{DS}$                          | 600          | V    |
| Gate-Source Voltage                                 |  |  |                        |  | $V_{GS}$                          | $\pm 30$     | V    |
| Continuous Drain Current <sup>(Note 1)</sup>        |  |  | T <sub>C</sub> = 25°C  |  | I <sub>D</sub>                    | 11           | A    |
|                                                     |  |  | T <sub>C</sub> = 100°C |  |                                   | 6.6          | A    |
| Pulsed Drain Current <sup>(Note 2)</sup>            |  |  |                        |  | I <sub>DM</sub>                   | 33           | A    |
| Total Power Dissipation @ T <sub>C</sub> = 25°C     |  |  |                        |  | P <sub>DTOT</sub>                 | 125          | W    |
| Single Pulsed Avalanche Energy <sup>(Note 3)</sup>  |  |  |                        |  | E <sub>AS</sub>                   | 169          | mJ   |
| Single Pulsed Avalanche Current <sup>(Note 3)</sup> |  |  |                        |  | I <sub>AS</sub>                   | 2.6          | A    |
| Operating Junction and Storage Temperature Range    |  |  |                        |  | T <sub>J</sub> , T <sub>STG</sub> | - 55 to +150 | °C   |

### THERMAL PERFORMANCE

| PARAMETER                              | SYMBOL          | Limit | UNIT |
|----------------------------------------|-----------------|-------|------|
| Junction to Case Thermal Resistance    | $R_{\theta JC}$ | 1.0   | °C/W |
| Junction to Ambient Thermal Resistance | $R_{\theta JA}$ | 62    | °C/W |

**Thermal Performance Note:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.  $R_{\theta JA}$  shown below for single device operation on FR-4 PCB in still air.

| ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted) |                                                                                                    |                     |     |      |      |      |
|--------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------|---------------------|-----|------|------|------|
| PARAMETER                                                                | CONDITIONS                                                                                         | SYMBOL              | MIN | TYP  | MAX  | UNIT |
| Static                                                                   |                                                                                                    |                     |     |      |      |      |
| Drain-Source Breakdown Voltage                                           | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                                                       | BV <sub>DSS</sub>   | 600 | --   | --   | V    |
| Gate Threshold Voltage                                                   | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                         | V <sub>GS(TH)</sub> | 2.0 | 3.1  | 4.0  | V    |
| Gate Body Leakage                                                        | V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V                                                       | I <sub>GSS</sub>    | --  | --   | ±100 | nA   |
| Zero Gate Voltage Drain Current                                          | V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V                                                       | I <sub>DSS</sub>    | --  | --   | 1    | μA   |
| Drain-Source On-State Resistance<br>(Note 4)                             | V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.5A                                                       | R <sub>DS(on)</sub> | --  | 0.31 | 0.38 | Ω    |
| Dynamic (Note 5)                                                         |                                                                                                    |                     |     |      |      |      |
| Total Gate Charge                                                        | V <sub>DS</sub> = 380V, I <sub>D</sub> = 11A,<br>V <sub>GS</sub> = 10V                             | Q <sub>g</sub>      | --  | 20.5 | --   | nC   |
| Gate-Source Charge                                                       |                                                                                                    | Q <sub>gs</sub>     | --  | 4.8  | --   |      |
| Gate-Drain Charge                                                        |                                                                                                    | Q <sub>gd</sub>     | --  | 6.5  | --   |      |
| Input Capacitance                                                        | V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                        | C <sub>iss</sub>    | --  | 1040 | --   | pF   |
| Output Capacitance                                                       |                                                                                                    | C <sub>oss</sub>    | --  | 66   | --   |      |
| Gate Resistance                                                          | F = 1MHz, open drain                                                                               | R <sub>g</sub>      | --  | 3.2  | --   | Ω    |
| Switching (Note 6)                                                       |                                                                                                    |                     |     |      |      |      |
| Turn-On Delay Time                                                       | V <sub>DD</sub> = 380V,<br>R <sub>GEN</sub> = 35Ω,<br>I <sub>D</sub> = 11A, V <sub>GS</sub> = 10V, | t <sub>d(on)</sub>  | --  | 24   | --   | ns   |
| Turn-On Rise Time                                                        |                                                                                                    | t <sub>r</sub>      | --  | 28   | --   |      |
| Turn-Off Delay Time                                                      |                                                                                                    | t <sub>d(off)</sub> | --  | 70   | --   |      |
| Turn-Off Fall Time                                                       |                                                                                                    | t <sub>f</sub>      | --  | 60   | --   |      |
| Source-Drain Diode                                                       |                                                                                                    |                     |     |      |      |      |
| Forward On Voltage (Note 4)                                              | I <sub>S</sub> = 11A, V <sub>GS</sub> = 0V                                                         | V <sub>SD</sub>     | --  | --   | 1.4  | V    |
| Reverse Recovery Time                                                    | V <sub>R</sub> =200V, I <sub>S</sub> = 5.5A<br>dI <sub>F</sub> /dt = 100A/μs                       | t <sub>rr</sub>     | --  | 210  | --   | ns   |
| Reverse Recovery Charge                                                  |                                                                                                    | Q <sub>rr</sub>     | --  | 1.8  | --   | μC   |

**Notes:**

- Current limited by package.
- Pulse width limited by the maximum junction temperature.
- $L = 50mH, I_{AS} = 2.6A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
- Pulse test:  $PW \leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

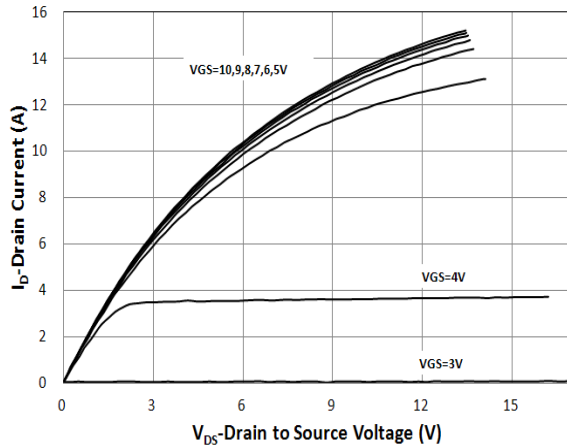
**ORDERING INFORMATION**

| PART NO.        | PACKAGE | PACKING      |
|-----------------|---------|--------------|
| TSM60N380CZ C0G | TO-220  | 50pcs / Tube |

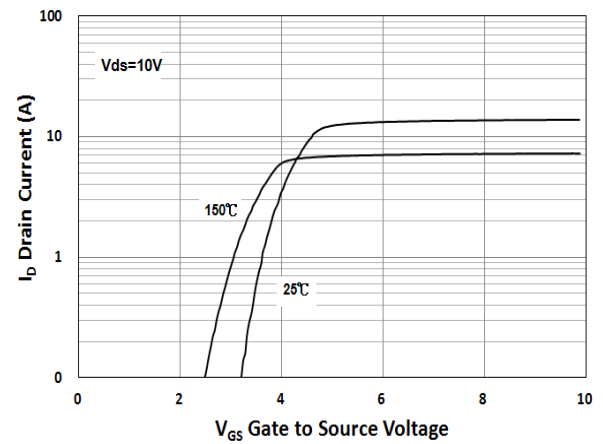
## CHARACTERISTICS CURVES

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

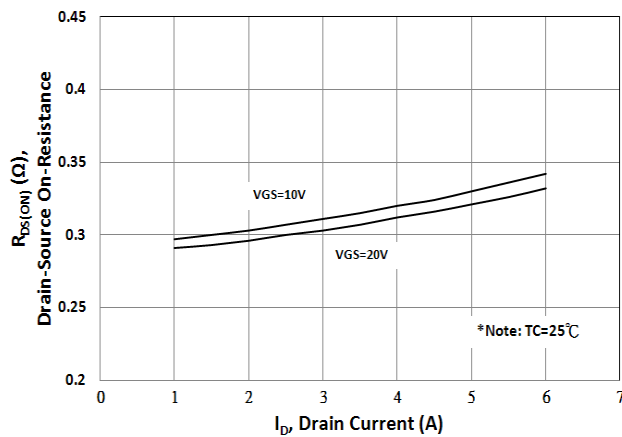
**Output Characteristics**



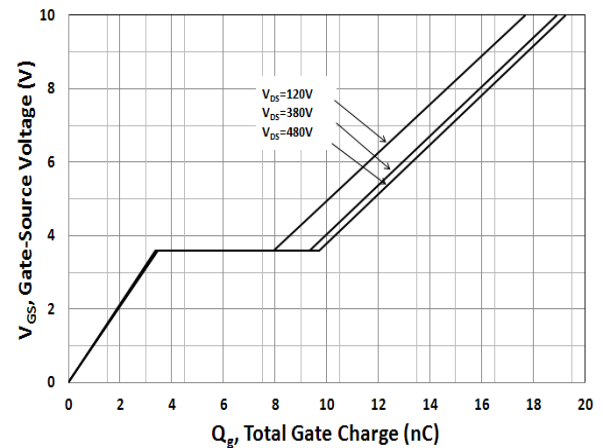
**Transfer Characteristics**



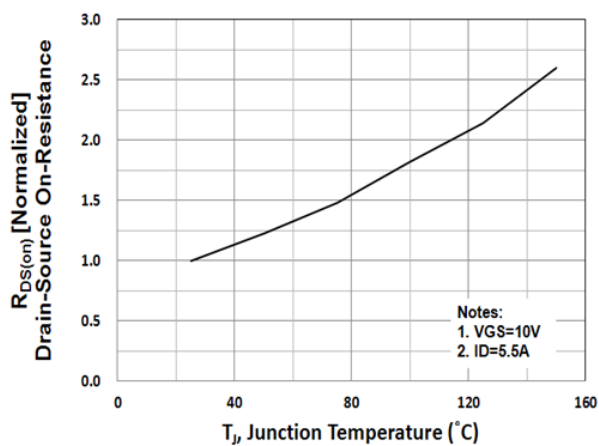
**On-Resistance vs. Drain Current**



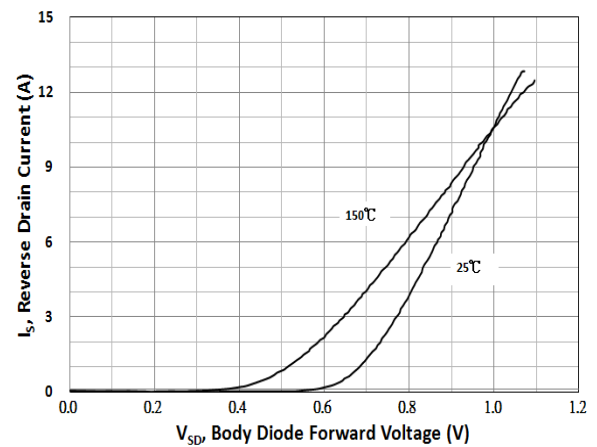
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



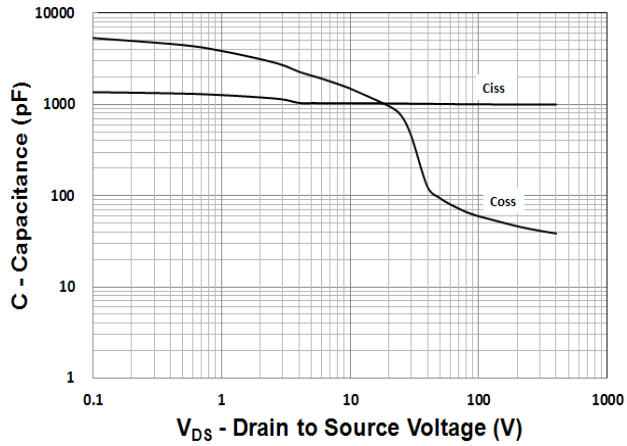
**Source-Drain Diode Forward Current vs. Voltage**



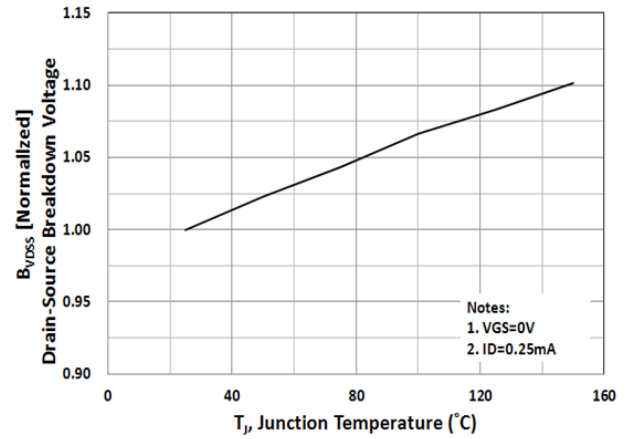
## CHARACTERISTICS CURVES

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

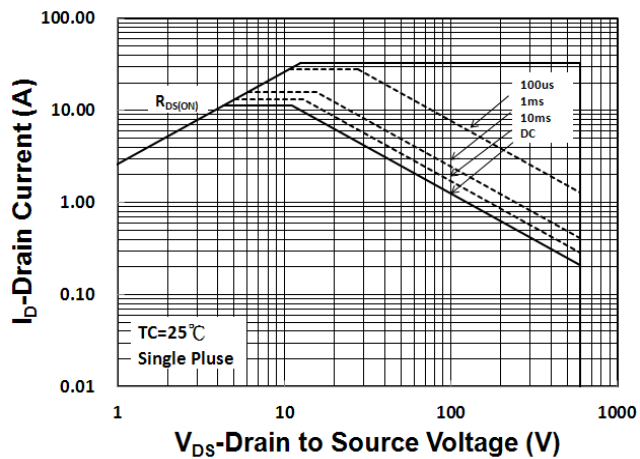
**Capacitance vs. Drain-Source Voltage**



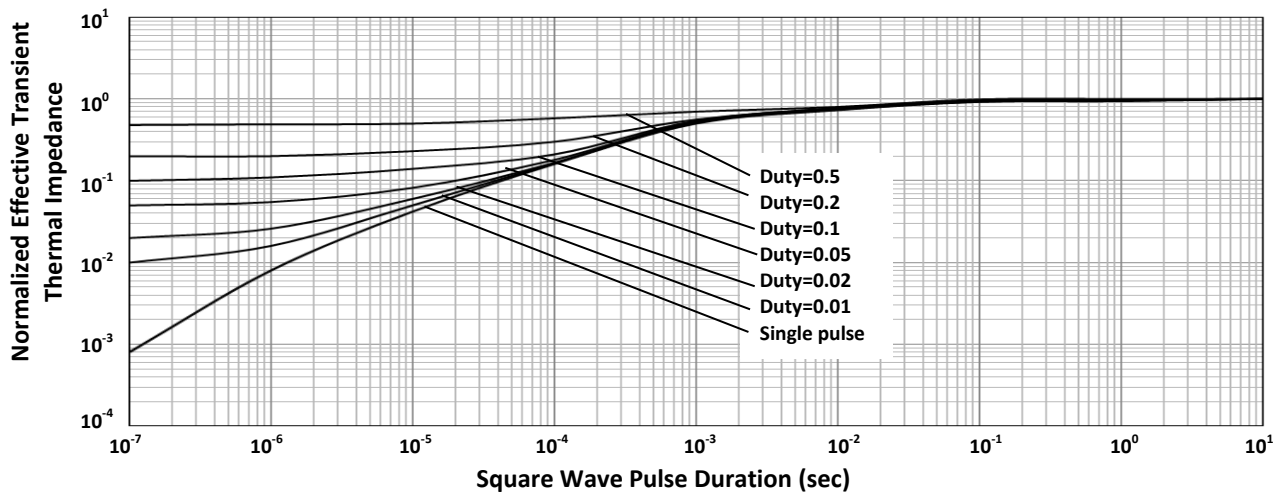
**$BV_{DSS}$  vs. Junction Temperature**



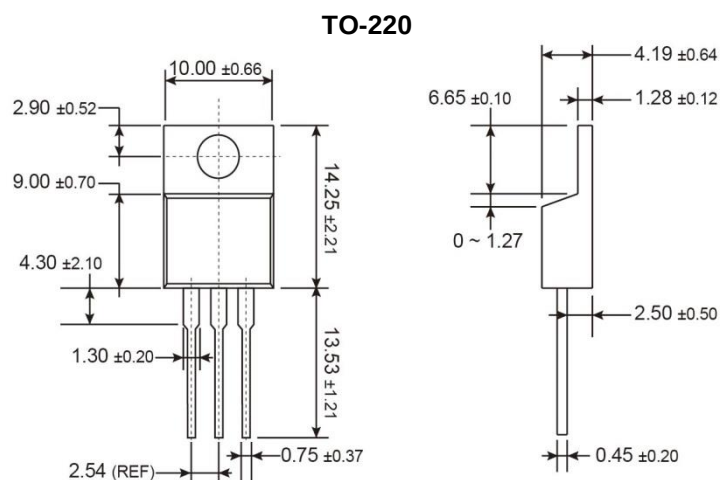
**Maximum Safe Operating Area**



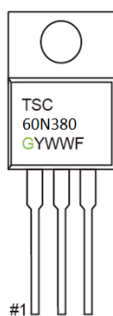
**Normalized Thermal Transient Impedance, Junction-to-Case**



**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)



**MARKING DIAGRAM**



- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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